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Semiconductor devices

Part 9: Discrete devices – Insulated-gate bipolar transistors (IGBTs)

bsi.

National foreword

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Part 9: Discrete devices – Insulated-gate bipolar transistors (IGBTs)

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CONTENTS

FOREWORD ... 7
1 Scope ... 9
2 Normative references ... 9
3 Terms and definitions ... 9
3.1 General terms ... 9
3.2 Terms related to ratings and characteristics, voltages and currents ... 10
3.3 Terms related to ratings and characteristics ... 13
4 Letter symbols ... 15
4.1 General ... 15
4.2 Graphical symbols ... 16
4.3 Additional general subscripts ... 16
4.4 List of letter symbols ... 16
4.4.1 Voltages ... 16
4.4.2 Currents ... 17
4.4.3 Other electrical magnitudes ... 17
4.4.4 Time ... 18
4.4.5 Thermal magnitudes ... 18
5 Essential ratings and characteristics ... 18
5.1 General ... 18
5.2 Ratings (limiting values) ... 18
5.2.1 General ... 18
5.2.2 Ambient or case or virtual junction operating temperature (T_a or T_c or T_{vj}) ... 18
5.2.3 Storage temperature (T_{stg}) ... 18
5.2.4 Collector-emitter voltage with gate-emitter short-circuited (V_{CES}) ... 18
5.2.5 Gate-emitter voltage with collector-emitter short-circuit (V_{GES}) ... 19
5.2.6 Continuous (direct) reverse voltage of a reverse-blocking IGBT (V_{R*}) ... 19
5.2.7 Continuous (direct) collector current (I_C) ... 19
5.2.8 Repetitive peak collector current (I_{CRM}) ... 19
5.2.9 Non-repetitive peak collector current (I_{CSM}) ... 19
5.2.10 Continuous (direct) reverse-conducting current of a reverse-conducting IGBT (I_{RC}) ... 19
5.2.11 Repetitive peak reverse-conducting current of a reverse-conducting IGBT (I_{RCRM}) ... 19
5.2.12 Non-repetitive peak reverse-conducting current of a reverse-conducting IGBT (I_{RCSM}) ... 19
5.2.13 Total power dissipation (P_{tot}) ... 19
5.2.14 Maximum forward biased safe operating area (FBSOA) (where appropriate) ... 19
5.2.15 Maximum reverse biased safe operating area (RBSOA) ... 19
5.2.16 Maximum short-circuit safe operating area (SCSOA) ... 20
5.2.17 Maximum terminal current (I_{tRMS}) (where appropriate) ... 20
5.2.18 Mounting force (F) ... 20
5.2.19 Mounting torque (M) ... 20
5.3 Characteristics ... 20
5.3.1 General ... 20
5.3.2 Collector-emitter breakdown voltage ($V_{(BR)CES}$) (where appropriate) ... 20

5.3.3 Collector-emitter sustaining voltage (V_{CE*sus}) (where appropriate) 20
5.3.4 Collector-emitter saturation voltage (V_{CEsat}) 20
5.3.5 Gate-emitter threshold voltage ($V_{GE(th)}$) 20
5.3.6 Reverse-conducting voltage of a reverse-conducting IGBT (V_{RC}) 20
5.3.7 Collector-emitter cut-off current (I_{CE*}) 20
5.3.8 Gate leakage current (I_{GES}) 20
5.3.9 Reverse current of a reverse-blocking IGBT (I_{R*}) 21
5.3.10 Capacitances 21
5.3.11 Gate charge (Q_G) 21
5.3.12 Internal gate resistance (r_g) 21
5.3.13 Switching characteristics 21
5.3.14 Thermal resistance junction to case ($R_{th(j-c)}$) 22
5.3.15 Thermal resistance junction to ambient ($R_{th(j-a)}$) 22
5.3.16 Transient thermal impedance junction to case ($Z_{th(j-c)}$) 22
5.3.17 Transient thermal impedance junction to ambient ($Z_{th(j-a)}$) 23
6 Measuring methods 23
6.1 General 23
6.2 Verification of ratings (limiting values) 23
6.2.1 General 23
6.2.2 Collector-emitter voltages (V_{CES}, V_{CER}, V_{CEX}) 23
6.2.3 Reverse voltage of a reverse-blocking IGBT (V_{RS}, V_{RX}) 24
6.2.4 Gate-emitter voltage with collector-emitter short-circuit ($\pm V_{GES}$) 25
6.2.5 Continuous (direct) collector current (I_C) 26
6.2.6 Maximum peak collector current (I_{CRM} and I_{CSM}) 27
6.2.7 Continuous (direct) reverse-conducting current of a reverse-conducing IGBT (I_{RC}) 28
6.2.8 Maximum peak reverse-conducting current of a reverse-conducting IGBT (I_{RCRM} and I_{RCSM}) 29
6.2.9 Maximum reverse biased safe operating area (RBSOA) 30
6.2.10 Maximum short-circuit safe operating area (SCSOA) 32
6.3 Methods of measurement 35
6.3.1 Collector-emitter saturation voltage (V_{CEsat}) 35
6.3.2 Gate-emitter threshold voltage ($V_{GE(th)}$) 36
6.3.3 Reverse-conducting voltage of a reverse-conducting IGBT (V_{RC}) 36
6.3.4 Collector cut-off current (I_{CES}, I_{CER}, I_{CEX}) 37
6.3.5 Gate leakage current (I_{GES}) 38
6.3.6 Reverse current of a reverse-blocking IGBT (I_{RS}, I_{RX}) 39
6.3.7 Input capacitance (C_{ies}) 40
6.3.8 Output capacitance (C_{oes}) 41
6.3.9 Reverse transfer capacitance (C_{res}) 43
6.3.10 Gate charge (Q_G) 43
6.3.11 Internal gate resistance (r_g) 45
6.3.12 Turn-on times ($t_{d(on)}$, t_r, t_{on}) and turn-on energy (E_{on}) 46
6.3.13 Turn-off times ($t_{d(off)}$, t_f, t_{off}, t_z) and turn-off energy (E_{off}) 48
6.3.14 Peak reverse recovery current (I_{rrm}), reverse recovery time (t_{rr}), reverse recovery energy (E_{rr}) and reverse recovered charge (Q_{rr}) of a reverse-blocking IGBT 49
6.3.15 Peak forward recovery current (I_{frm}), forward recovery time (t_{fr}), forward recovery energy (E_{fr}) and forward recovered charge (Q_{fr}) of a reverse-conducting IGBT 52

6.3.16 Thermal resistance junction to case ($R_{th(j-c)}$) and transient thermal impedance junction to case ($Z_{th(j-c)}$) ... 54
7 Acceptance and reliability ... 60
7.1 General requirements ... 60
7.2 Specific requirements ... 60
7.2.1 List of endurance and reliability tests ... 60
7.2.2 Conditions for endurance and reliability tests ... 60
7.2.3 Acceptance-defining characteristics and criteria for endurance and reliability tests ... 60
7.2.4 Procedure in case of a testing error ... 61
7.2.5 Endurance and reliability tests and test methods ... 61
7.3 Type tests and routine tests ... 64
7.3.1 Type tests ... 64
7.3.2 Routine tests ... 65
Annex A (normative) Measuring method for collector-emitter breakdown voltage ... 66
A.1 General ... 66
A.2 Purpose ... 66
A.3 Circuit diagram ... 66
A.4 Measurement procedure ... 66
A.5 Specified conditions ... 67
Annex B (normative) Measuring method for collector-emitter sustaining voltage ... 68
B.1 General ... 68
B.2 Purpose ... 68
B.3 Circuit diagram ... 68
B.4 Circuit description and requirements ... 68
B.5 Measurement procedure ... 69
B.6 Precautions to be observed ... 69
B.7 Requirements ... 69
B.8 Specified conditions ... 70
Annex C (normative) Measuring method for inductive load turn-off current under specified conditions ... 71
C.1 General ... 71
C.2 Purpose ... 71
C.3 Circuit diagram and waveforms ... 71
C.4 Circuit description and requirements ... 72
C.5 Measurement procedure ... 72
C.6 Specified conditions ... 72
Annex D (normative) Forward biased safe operating area (FBSOA) ... 73
D.1 General ... 73
D.2 Purpose ... 73
D.3 Method 1 ... 73
D.3.1 General ... 73
D.3.2 Circuit diagram ... 73
D.3.3 Test procedure ... 74
D.3.4 Specified conditions ... 75
D.4 Method 2 ... 75
D.4.1 General ... 75
D.4.2 Circuit diagram ... 75
D.4.3 Test procedure and precautions to be taken ... 76

D.4.4 Specified conditions ... 77
Bibliography ... 78

Figure 1 – Graphical symbols ... 16
Figure 2 – Circuit for testing the collector-emitter voltages V_{CES}, V_{CER}, V_{CEX} ... 24
Figure 3 – Circuit for testing the reverse voltages V_{RS}, V_{RX} ... 25
Figure 4 – Circuit for testing the gate-emitter voltage $\pm V_{GES}$ ... 26
Figure 5 – Circuit for testing collector current ... 27
Figure 6 – Circuit for testing peak collector current ... 28
Figure 7 – Circuit for testing reverse-conducting current ... 28
Figure 8 – Circuit for testing peak reverse-conducting current ... 29
Figure 9 – Circuit for testing reverse biased safe operating area (RBSOA) ... 30
Figure 10 – Waveforms of gate-emitter voltage V_{GE} and collector current I_C during turn-off ... 31
Figure 11 – Circuit for testing safe operating pulse width at load short-circuit (SCSOA1) ... 32
Figure 12 – Waveforms of gate-emitter voltage V_{GE}, collector current I_C and collector-emitter voltage V_{CE} during load short-circuit condition SCSOA1 ... 32
Figure 13 – Circuit for testing short-circuit safe operating area 2 (SCSOA2) ... 33
Figure 14 – Waveforms during SCSOA2 ... 34
Figure 15 – Circuit for measuring the collector-emitter saturation voltage V_{CEsat} ... 35
Figure 16 – Circuit for measuring the gate-emitter threshold voltage ... 36
Figure 17 – Circuit for measuring the reverse-conducting voltage V_{RC} ... 37
Figure 18 – Circuit for measuring the collector cut-off current ... 38
Figure 19 – Circuit for measuring the gate leakage current ... 39
Figure 20 – Circuit for measuring the reverse current ... 40
Figure 21 – Circuit for measuring the input capacitance ... 41
Figure 22 – Circuit for measuring the output capacitance ... 42
Figure 23 – Circuit for measuring the reverse transfer capacitance ... 43
Figure 24 – Circuit for measuring the gate charge ... 44
Figure 25 – Basic gate charge waveform ... 44
Figure 26 – Circuit for measuring the internal gate resistance ... 45
Figure 27 – Circuit for measuring turn-on times and energy ... 46
Figure 28 – Waveforms during turn-on times ... 47
Figure 29 – Circuit for measuring turn-off times and energy ... 48
Figure 30 – Waveforms during turn-off times ... 48
Figure 31 – Circuit for measuring reverse recovery characteristics ... 50
Figure 32 – Waveforms during reverse recovery ... 50
Figure 33 – Circuit for measuring forward recovery characteristics ... 52
Figure 34 – Waveforms during forward recovery ... 53
Figure 35 – Circuit for measuring the variation with temperature of the collector-emitter voltage V_{CE} at a low measuring current I_{C1} and for heating up the IGBT by a high current I_{C2} ... 55
Figure 36 – Typical variation of the collector-emitter voltage V_{CE} at a low measuring current I_{C1} with the case temperature T_c (when heated from outside, i.e. $T_c = T_{vj}$) ... 56
Figure 37 – I_C, V_{CE} and T_c with time ... 57

Figure 38 – Circuit for measuring thermal resistance and transient thermal impedance: Method 2 ... 58
Figure 39 – Typical variation of the gate-emitter threshold voltage $V_{GE(th)}$ at a low measuring current I_{C1} with the case temperature T_c (when heated from the outside, i.e. $T_c = T_{vj}$) ... 59
Figure 40 – I_C, V_{GE} and T_c with time ... 60
Figure 41 – Circuit for high-temperature blockings ... 62
Figure 42 – Circuit for high-temperature gate bias ... 63
Figure 43 – Circuit for intermittent operating life ... 64
Figure 44 – Expected number of cycles versus temperature rise ΔT_{vj} ... 64
Figure A.1 – Circuit for measuring the collector-emitter breakdown voltage ... 66
Figure B.1 – Circuit for measuring the collector-emitter sustaining voltage V_{CE*sus} ... 68
Figure B.2 – Operating locus of the collector current ... 69
Figure C.1 – Circuit for measuring inductive load turn-off current ... 71
Figure C.2 – Waveforms of collector current I_C and collector voltage V_{CE} during turn-off ... 72
Figure D.1 – Circuit for testing forward biased safe operating area (method 1) ... 73
Figure D.2 – Typical ΔV_{CE} versus collector-emitter voltage V_{CE} characteristics ... 74
Figure D.3 – Typical forward biased safe operating area ... 75
Figure D.4 – Circuit for testing forward biased safe operating area (method 2) ... 76
Figure D.5 – Latching mode operation waveforms ... 76
Figure D.6 – Latching mode I-V characteristics ... 76

Table 1 – Acceptance defining characteristics ... 23
Table 2 – Acceptance-defining characteristics for endurance and reliability tests ... 61
Table 3 – Minimum type and routine tests for IGBTs when applicable ... 65

INTERNATIONAL ELECTROTECHNICAL COMMISSION

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SEMICONDUCTOR DEVICES –

Part 9: Discrete devices – Insulated-gate bipolar transistors (IGBTs)

FOREWORD

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International Standard IEC 60747-9 has been prepared by subcommittee 47E: Discrete semiconductor devices, of IEC technical committee 47: Semiconductor devices.

This third edition cancels and replaces the second edition published in 2007. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

a) reverse-blocking IGBT and its related technical contents have been added;
b) reverse-conducting IGBT and its related technical contents have been added;
c) some parts of the previous edition have been amended, combined or deleted.

The text of this International Standard is based on the following documents:

FDIS	Report on voting
47E/675/FDIS	47E/684/RVD

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 60747 series, published under the general title: *Semiconductor devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "http://webstore.iec.ch" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

SEMICONDUCTOR DEVICES –

Part 9: Discrete devices – Insulated-gate bipolar transistors (IGBTs)

1 Scope

This part of IEC 60747 specifies product specific standards for terminology, letter symbols, essential ratings and characteristics, verification of ratings and methods of measurement for insulated-gate bipolar transistors (IGBTs).

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 60747-1:2006, *Semiconductor devices – Part 1: General*
IEC 60747-1:2006/AMD1:2010

IEC 61340 (all parts), *Electrostatics*

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at http://www.electropedia.org/
- ISO Online browsing platform: available at http://www.iso.org/obp

3.1 General terms

3.1.1
insulated-gate bipolar transistor
IGBT
transistor having a conductive channel and one PN junction in the forward direction and another PN junction in the reverse direction, the current flowing through the channel and the junction being controlled by an electric field resulting from a voltage applied between the gate and emitter terminals

Note 1 to entry: With collector-emitter voltage applied, the collector side PN junction is forward biased.

Note 2 to entry: This note applies to the French language only.

3.1.2
N-channel IGBT
IGBT that has one or more N-type conduction channels

[SOURCE: IEC 60050-521:2002, 521-04-56, modified – reworded for IGBT.]